

AMENDMENTS TO THE CLAIMS:

Please amend Claims 1, 9, and 10 as follows;

1. (Currently Amended) A solid state image pick-up device formed on a chip, comprising:
 - a pixel region;
 - a first shift register horizontal scanning circuits arranged along sides of the chip sandwiching the pixel region for reading a signal charge from the pixel region;
 - a second shift register vertical scanning circuit arranged along a side of the chip not parallel to the side of the chip and along which none of the horizontal scanning circuits is arranged, and having a lower driving frequency than that of the horizontal scanning circuits first shift register; wherein the first and second shift registers are arranged along respectively different side portions of the chip;
 - an amplifier for amplifying the signal charge read from the pixel region by the horizontal scanning circuits first shift register, outputting video signals; and
 - a pad for outputting the video signals to an outside of the chip, the pad being arranged only along a side portion of the chip not parallel to the side portion along which the first shift register is arranged of the chip along which none of the horizontal scanning circuits and the vertical scanning circuit is arranged.
2. (Previously Presented) The solid state image pick-up device according to claim 1, wherein in the pixel region, pixels having an active element are two-dimensionally arranged.

3. (Previously Presented) The solid state image pick-up device according to claim 2, wherein the active element comprises at least one selected from the group consisting of a transfer MOS transistor, a reset MOS transistor, a source follower input MOS transistor, and a selection MOS transistor.

4. (Cancelled)

5. (Previously Presented) The solid state image pick-up device according to claim 2, wherein the pixel region is formed into a rectangle, and the first shift register is arranged closer to a long side of the pixel region.

6. (Previously Presented) The solid state image pick-up device according to claim 5, wherein the pixel region is sandwiched by shift registers.

7. (Previously Presented) The solid state image pick-up device according to claim 2, wherein the first shift register is a horizontal shift register, and the second shift register is a vertical shift register.

8. (Original) A camera, comprising:
the solid state image pick-up device according to claim 1;
a lens for forming an optical image of a subject; and
a signal processing unit for processing a signal from the solid state image pick-up device.

9. (Currently Amended) A solid state image pick-up device formed on a chip, comprising:

a pixel region;

a first shift register horizontal scanning circuits arranged along sides of the chip sandwiching the pixel region for reading a signal charge from the pixel region;

a second shift register vertical scanning circuit arranged along a side of the chip not parallel to the side of the chip and along which none of the horizontal scanning circuits is arranged, and having a lower driving frequency than that of the horizontal scanning circuits first shift register; wherein the first and second shift registers are arranged along respectively different side portions of the chip;

an amplifier for amplifying the signal charge read from the pixel region by the horizontal scanning circuits first shift register, outputting video signals; and

a pad for supplying a voltage to the amplifier, the pad being arranged only along a side portion of the chip not parallel to the side portion along which the first shift register is arranged of the chip along which none of the horizontal scanning circuits and the vertical scanning circuit is arranged.

10. (Currently Amended) A solid state image pick-up device formed on a chip, comprising:

a pixel region;

a first shift register horizontal scanning circuits arranged along sides of the chip sandwiching the pixel region for reading a signal charge from the pixel region;

a second shift register vertical scanning circuit arranged along a side of the chip not parallel to the side of the chip and along which none of the horizontal scanning circuits

is arranged, and having a lower driving frequency than that of the horizontal scanning circuits first shift register; wherein the first and second shift registers are arranged along respectively different side portions of the chip;

an amplifier for amplifying the signal charge read from the pixel region by the horizontal scanning circuits first shift register, outputting video signals; and

a pad for supplying a predetermined voltage or a ground voltage to an active element included in a pixel in the pixel region, the pad being arranged only along a side portion of the chip not parallel to the side portion along which the first shift register is arranged of the chip along which none of the horizontal scanning circuits and the vertical scanning circuit is arranged.

11. (Previously Presented) The solid state image pick-up device according to claim 1, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.

12. (Previously Presented) The solid state image pick-up device according to claim 9, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.

13. (Previously Presented) The solid state image pick-up device according to claim 10, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.

14. (Previously Presented) The solid state image pick-up device according to claim 1, wherein the pad is arranged only along a side portion of the chip at an angle of 90 degrees to the side portion along which the first shift register is arranged.

15. (Previously Presented) The solid state image pick-up device according to claim 9, wherein the pad is arranged only along a side portion of the chip at an angle of 90 degrees to the side portion along which the first shift register is arranged.

16. (Previously Presented) The solid state image pick-up device according to claim 10, wherein the pad is arranged only along a side portion of the chip at an angle of 90 degrees to the side portion along which the first shift register is arranged.